

IN THE CLAIMS:

Please amend claims 1, 5, 11 and 14 as follows:

1. (Amended) A method of manufacturing a semiconductor device comprising the steps

forming an impurity diffusion layer in a semiconductor substrate;

forming a first insulating film covering the semiconductor substrate;

(forming a lower electrode of a capacitor on the first insulating film;) missing

forming an oxide dielectric film of the capacitor on the lower electrode;

forming an upper electrode of the capacitor on the oxide dielectric film;

forming a second insulating film for covering the capacitor;

forming a first opening [on or above] which exposes the impurity diffusion layer and a second opening [on] which exposes the upper electrode in the first and second insulating films, by etching a part of the second insulating film and a part of the first insulating film;

forming [an] a [oxidation-preventing] metal film on the second insulating film for connecting electrically the impurity diffusion layer via the first opening and the upper electrode via the second opening;

forming a local interconnection in a range which passes through the first opening and the second opening and contains at least a region where the upper electrode contacts with the oxide dielectric film, by patterning the [oxidation-preventing] metal film; and

A1 cancelled
forming a third insulating film for covering the local interconnection.

Claim 5, line 9, please change "the" to --a--.

Claim 11, line 4, please change "the" to --an--.

Claim 14, line 5, before "diffusion", please insert --impurity--.

Please add new claim 21 as follows:

Sub B2
-21. A method of manufacturing a semiconductor device comprising the steps

A2
forming an impurity diffusion layer in a semiconductor substrate;

forming a first insulating film covering the semiconductor substrate;

forming a lower electrode of a capacitor on the first insulating film;

forming an oxide dielectric film of the capacitor on the lower electrode;

forming an upper electrode of the capacitor on the oxide dielectric film;

forming a second insulating film for covering the capacitor;

forming a first opening which exposes the impurity diffusion layer and a second opening which exposes the upper electrode in the first and second insulating films, by etching a part of the second insulating film and a part of the first insulating film;

forming a metal film on the second insulating film for connecting electrically the impurity diffusion layer via the first opening and the upper electrode via the second opening;